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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

In re application of: Ni *et al.*

Application No.: 09/347,583

Filed: June 30, 1999



Attorney Docket No.:
LAM1P111/P0513

Examiner: C. Brown

Group: 1765

Title: MOVEABLE BARRIER FOR MULTIPLE ETCH
PROCESSES

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
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Signed:

Natalie Morgan

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AMENDMENT

Assistant Commissioner for Patents
Box Amendment Fee
Washington, D.C. 20231

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Sir:

This is in response to the Office Action mailed October, 11 2000.
Reconsideration of the captioned application is respectfully requested.

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REMARKS

Claims 1-13 have been rejected by the Examiner. Claims 1-13 are pending in
this Application.

As mentioned on pages 1-3 of the Specification, the present invention relates
to a diffusion barrier that can be positioned in multiple positions relative to the wafer.
One known approach for improving etch rate uniformity in a chemically driven etch
process is to install a diffusion barrier around the wafer perimeter. However,
diffusion barriers are not used during ion-assisted (or ion-driven) etch processes (e.g.
a plasma enhanced etch process). More specifically, the diffusion barrier is believed
to quench the plasma and thus disturb the ion density uniformity in the plasma. If the
barrier were to be used, the plasma density near the wafer perimeter would be lowered
and thus cause a non-uniform etching during an ion assisted/driven etch. Because the